8-Bit Shift Register with Output Storage Register (3-State)

MC74VHC595

The MC74VHC595 is an advanced high speed 8–bit shift register with an output storage register fabricated with silicon gate CMOS technology.

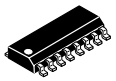
It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHC595 contains an 8–bit static shift register which feeds an 8–bit storage register.

Shift operation is accomplished on the positive going transition of the Shift Clock input (SCK). The output register is loaded with the contents of the shift register on the positive going transition of the Register Clock input (RCK). Since the RCK and SCK signals are independent, parallel outputs can be held stable during the shift operation. And, since the parallel outputs are 3–state, the VHC595 can be directly connected to an 8–bit bus. This register can be used in serial–to–parallel conversion, data receivers, etc.

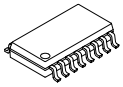
The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

- High Speed: f_{max} = 185MHz (Typ) at V_{CC} = 5V
- Low Power Dissipation: I_{CC} = 4μA (Max) at T_A = 25°C
- High Noise Immunity: $V_{NIH} = V_{NIL}$ = 28% V_{CC}
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2V to 5.5V Operating Range
- Low Noise: V_{OLP} = 1.0V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; Machine Model > 200V
- Chip Complexity: 328 FETs or 82 Equivalent Gates



D SUFFIX
16–LEAD SOIC PACKAGE
CASE 751B–05

DT SUFFIX
16–LEAD TSSOP PACKAGE
CASE 948F–01

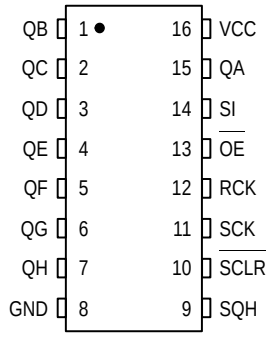


M SUFFIX
16–LEAD SOIC EIAJ PACKAGE
CASE 966–01

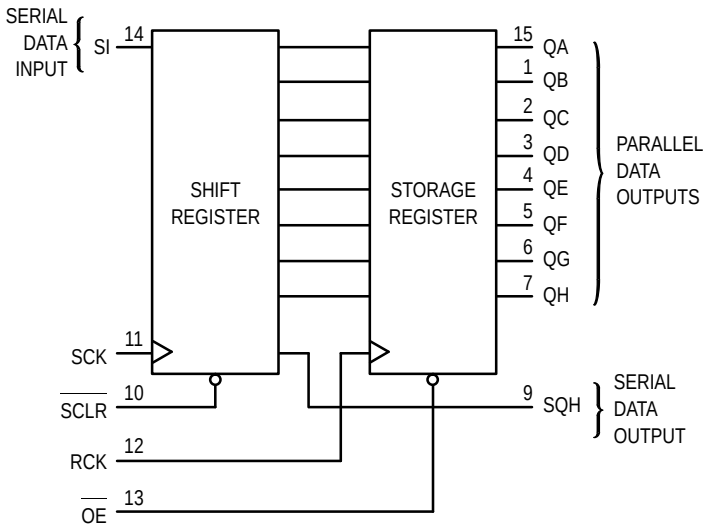
ORDERING INFORMATION

MC74VHCXXXD	SOIC
MC74VHCXXXDT	TSSOP
MC74VHCXXXM	SOIC EIAJ

PIN ASSIGNMENT



LOGIC DIAGRAM



MOTOROLA

FUNCTION TABLE

Operation	Inputs					Resulting Function			
	Reset (SCLR)	Serial Input (SI)	Shift Clock (SCK)	Reg Clock (RCK)	Output Enable (OE)	Shift Register Contents	Storage Register Contents	Serial Output (SQH)	Parallel Outputs (QA – QH)
Clear shift register	L	X	X	L, H, ↓	L	L	U	L	U
Shift data into shift register	H	D	↑	L, H, ↓	L	$D \rightarrow SR_A$; $SR_N \rightarrow SR_{N+1}$	U	$SR_G \rightarrow SR_H$	U
Registers remains unchanged	H	X	L, H, ↓	X	L	U	**	U	**
Transfer shift register contents to storage register	H	X	L, H, ↓	↑	L	U	$SR_N \rightarrow STR_N$	*	SR_N
Storage register remains unachanged	X	X	X	L, H, ↓	L	*	U	*	U
Enable parallel outputs	X	X	X	X	L	*	**	*	Enabled
Force outputs into high impedance state	X	X	X	X	H	*	**	*	Z

SR = shift register contents D = data (L, H) logic level ↓ = High–to–Low * = depends on Reset and Shift Clock inputs
STR = storage register contents U = remains unchanged ↑ = Low–to–High ** = depends on Register Clock input

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	– 0.5 to + 7.0	V
V_{in}	DC Input Voltage	– 0.5 to + 7.0	V
V_{out}	DC Output Voltage	– 0.5 to V_{CC} + 0.5	V
I_{IK}	Input Diode Current	– 20	mA
I_{OK}	Output Diode Current	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air, SOIC Packages†	500	mW
	TSSOP Package†	450	
T_{stg}	Storage Temperature	– 65 to + 150	°C

* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute–maximum–rated conditions is not implied.

†Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C
TSSOP Package: – 6.1 mW/°C from 65° to 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage		2.0	5.5	V
V_{in}	DC Input Voltage		0	5.5	V
V_{out}	DC Output Voltage		0	V_{CC}	V
T_A	Operating Temperature, All Package Types		– 40	+ 85	°C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 3.3V ±0.3V	0	100	ns/V
		V_{CC} =5.0V ±0.5V	0	20	

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} V	T_A = 25°C			T_A = – 40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
V_{IH}	Minimum High–Level Input Voltage		2.0 3.0 to 5.5	1.50 V_{CC} x 0.7			1.50 V_{CC} x 0.7		V
V_{IL}	Maximum Low–Level Input Voltage		2.0 3.0 to 5.5			0.50 V_{CC} x 0.3		0.50 V_{CC} x 0.3	V
V_{OH}	Minimum High–Level Output Voltage	V_{in} = V_{IH} or V_{IL} I_{OH} = – 50μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		V_{in} = V_{IH} or V_{IL} I_{OH} = – 4mA I_{OH} = – 8mA	 3.0 4.5	 2.58 3.94			 2.48 3.80		
V_{OL}	Maximum Low–Level Output Voltage	V_{in} = V_{IH} or V_{IL} I_{OL} = 50μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
		V_{in} = V_{IH} or V_{IL} I_{OL} = 4mA I_{OL} = 8mA	 3.0 4.5			 0.36 0.36		 0.44 0.44	
I_{OZ}	Three–State Output Off–State Current	V_{in} = V_{IH} or V_{IL} V_{out} = V_{CC} or GND	5.5			± 0.25		± 2.50	μA
I_{in}	Maximum Input Leakage Current	V_{in} = 5.5V or GND	0 to 5.5			± 0.1		± 1.0	μA
I_{CC}	Maximum Quiescent Supply Current	V_{in} = V_{CC} or GND	5.5			4.0		40.0	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0 ns)

Symbol	Parameter	Test Conditions		T_A = 25°C			T_A = – 40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
f_{max}	Maximum Clock Frequency (50% Duty Cycle)	V_{CC} = 3.3 ± 0.3V R_L = 1kΩ	C_L = 15pF C_L = 50pF	80 55	150 130		70 50		MHz
		V_{CC} = 5.0 ± 0.5V R_L = 1kΩ	C_L = 15pF C_L = 50pF	135 95	185 155		115 85		
t_{PLH}, t_{PHL}	Propagation Delay, SCK to SQH	V_{CC} = 3.3 ± 0.3V	C_L = 15pF C_L = 50pF		8.8 11.3	13.0 16.5	1.0 1.0	15.0 18.5	ns
		V_{CC} = 5.0 ± 0.5V	C_L = 15pF C_L = 50pF		6.2 7.7	8.2 10.2	1.0 1.0	9.4 11.4	
t_{PHL}	Propagation Delay, SCLR to SQH	V_{CC} = 3.3 ± 0.3V	C_L = 15pF C_L = 50pF		8.4 10.9	12.8 16.3	1.0 1.0	13.7 17.2	ns
		V_{CC} = 5.0 ± 0.5V	C_L = 15pF C_L = 50pF		5.9 7.4	8.0 10.0	1.0 1.0	9.1 11.1	
t_{PLH}, t_{PHL}	Propagation Delay, RCK to QA – QH	V_{CC} = 3.3 ± 0.3V	C_L = 15pF C_L = 50pF		7.7 10.2	11.9 15.4	1.0 1.0	13.5 17.0	ns
		V_{CC} = 5.0 ± 0.5V	C_L = 15pF C_L = 50pF		5.4 6.9	7.4 9.4	1.0 1.0	8.5 10.5	
t_{PZL}, t_{PZH}	Output Enable Time, OE to QA – QH	V_{CC} = 3.3 ± 0.3V R_L = 1kΩ	C_L = 15pF C_L = 50pF		7.5 9.0	11.5 15.0	1.0 1.0	13.5 17.0	ns
		V_{CC} = 5.0 ± 0.5V R_L = 1kΩ	C_L = 15pF C_L = 50pF		4.8 8.3	8.6 10.6	1.0 1.0	10.0 12.0	

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

Symbol	Parameter	Test Conditions	$T_A = 25°C$			$T_A = -40$ to $85°C$		Unit
			Min	Typ	Max	Min	Max	
t_{PLZ}, t_{PHZ}	Output Disable Time, OE to QA – QH	$V_{CC} = 3.3 \pm 0.3V$ $C_L = 50pF$ $R_L = 1k\Omega$		12.1	15.7	1.0	16.2	ns
		$V_{CC} = 5.0 \pm 0.5V$ $C_L = 50pF$ $R_L = 1k\Omega$		7.6	10.3	1.0	11.0	
C_{in}	Input Capacitance			4	10		10	pF
C_{out}	Three–State Output Capacitance (Output in High–Impedance State), QA – QH			6			10	

		Typical @ 25°C, $V_{CC} = 5.0V$	
C_{PD}	Power Dissipation Capacitance (Note 1.)	87	pF

1. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ns, $C_L = 50$pF, $V_{CC} = 5.0V$)

Symbol	Characteristic	$T_A = 25°C$		Unit
		Typ	Max	
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.8	1.0	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	– 0.8	– 1.0	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

TIMING REQUIREMENTS (Input $t_r = t_f = 3.0$ns)

Symbol	Parameter	V_{CC} V	$T_A = 25°C$		$T_A = -40$ to $85°C$	Unit
			Typ	Limit	Limit	
t_{su}	Setup Time, SI to SCK	3.3 5.0		3.5 3.0	3.5 3.0	ns
$t_{su(H)}$	Setup Time, SCK to RCK	3.3 5.0		8.0 5.0	8.5 5.0	ns
$t_{su(L)}$	Setup Time, SCLR to RCK	3.3 5.0		8.0 5.0	9.0 5.0	ns
t_h	Hold Time, SI to SCK	3.3 5.0		1.5 2.0	1.5 2.0	ns
$t_{h(L)}$	Hold Time, SCLR to RCK	3.3 5.0		0 0	0 0	ns
t_{rec}	Recovery Time, $\overline{SCLR}$ to SCK	3.3 5.0		3.0 2.5	3.0 2.5	ns
t_w	Pulse Width, SCK or RCK	3.3 5.0		5.0 5.0	5.0 5.0	ns
$t_{w(L)}$	Pulse Width, $\overline{SCLR}$	3.3 5.0		5.0 5.0	5.0 5.0	ns

SWITCHING WAVEFORMS

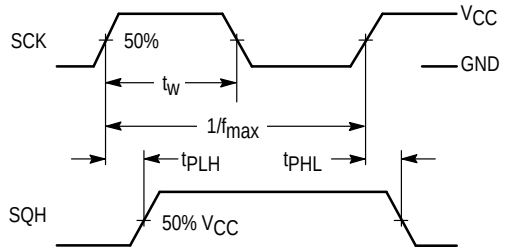


Figure 1.

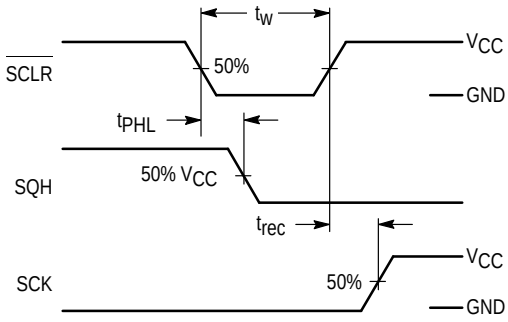


Figure 2.

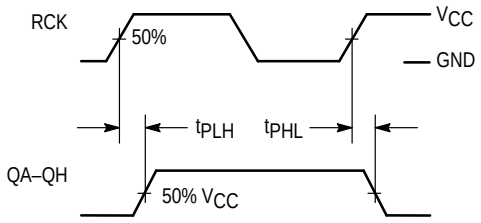


Figure 3.

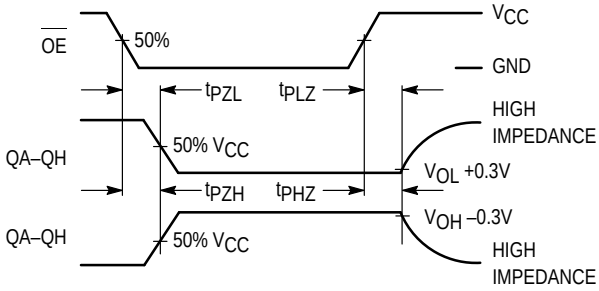


Figure 4.

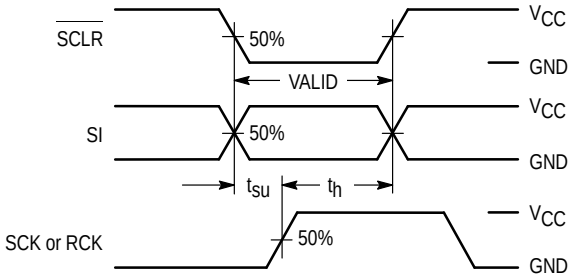


Figure 5.

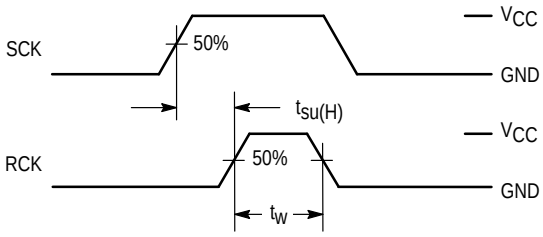
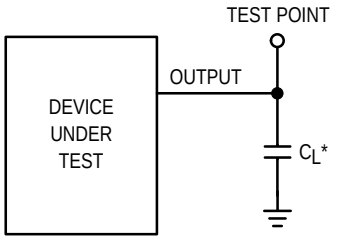


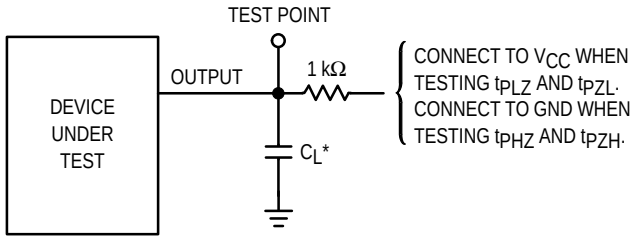
Figure 6.

TEST CIRCUITS



* Includes all probe and jig capacitance

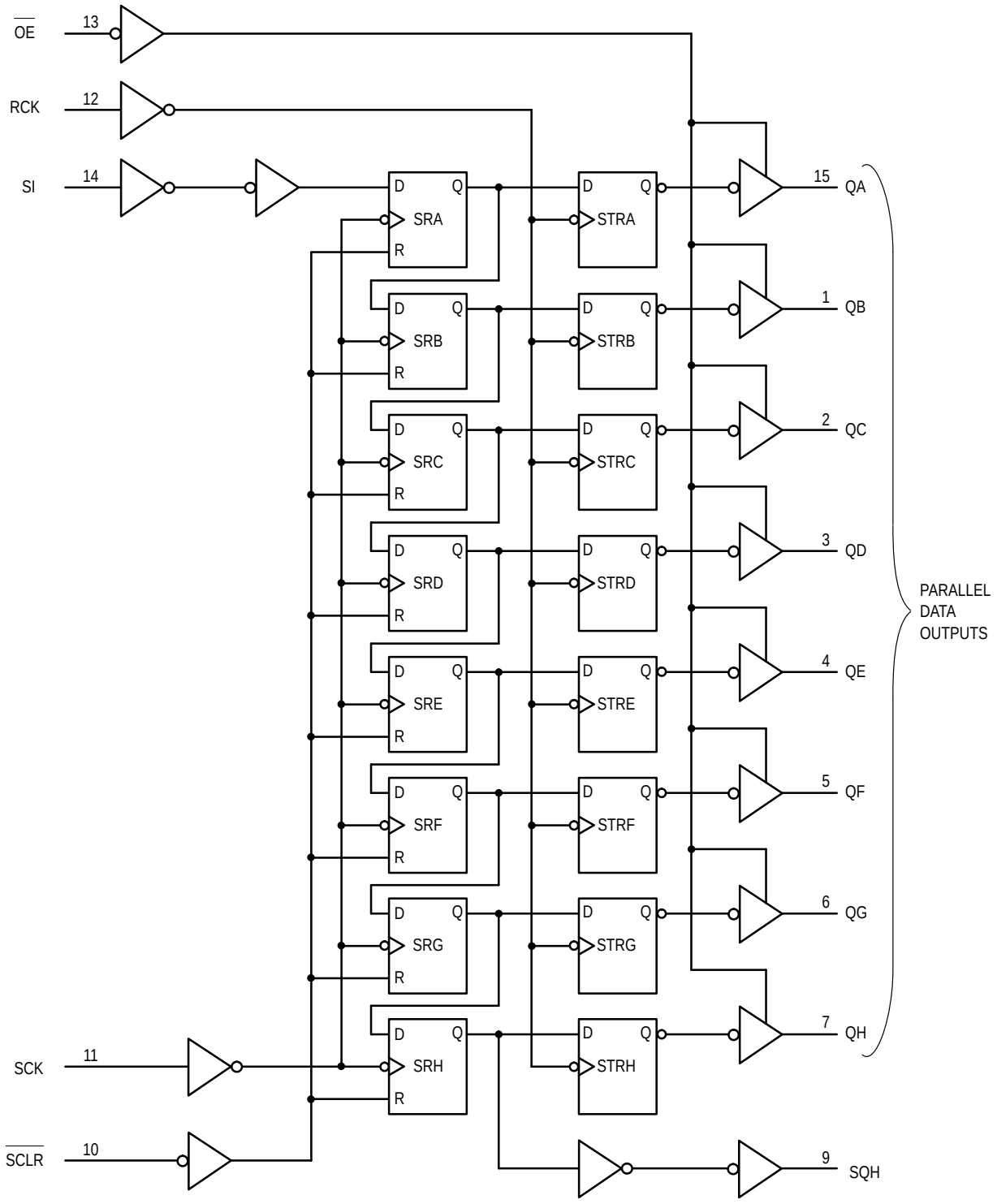
Figure 7.



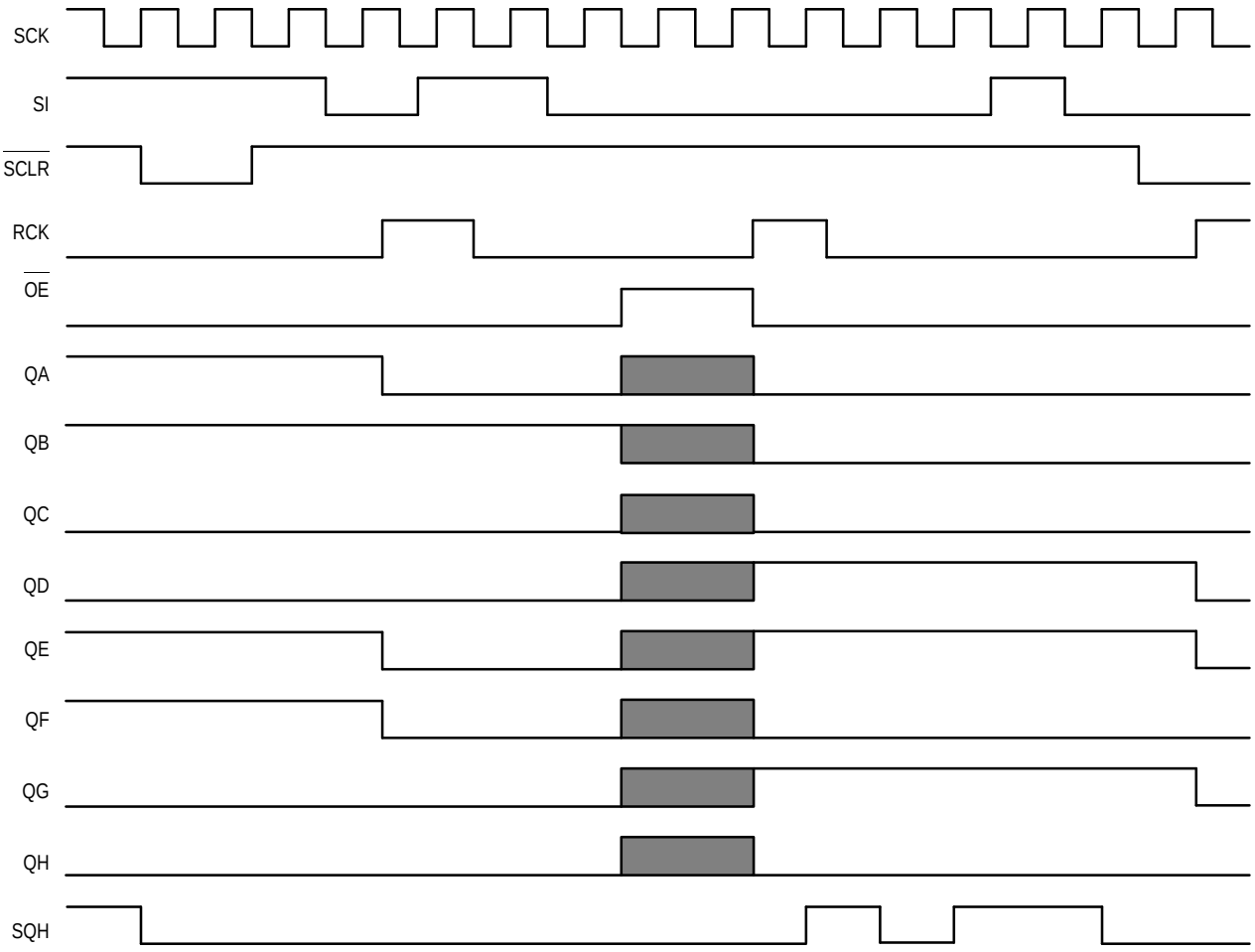
* Includes all probe and jig capacitance

Figure 8.

EXPANDED LOGIC DIAGRAM

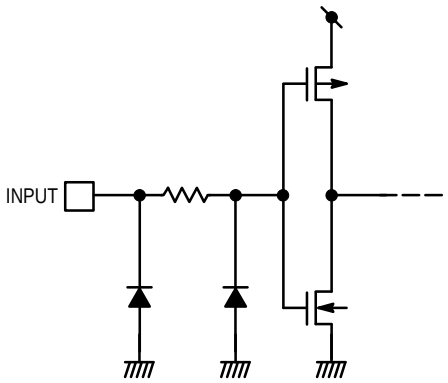


TIMING DIAGRAM



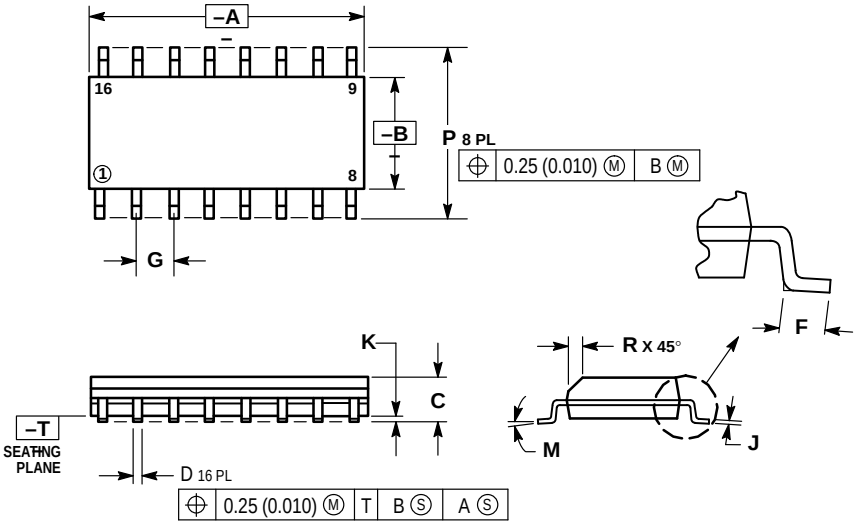
NOTE: ▭ output is in a high–impedance state.

INPUT EQUIVALENT CIRCUIT



OUTLINE DIMENSIONS

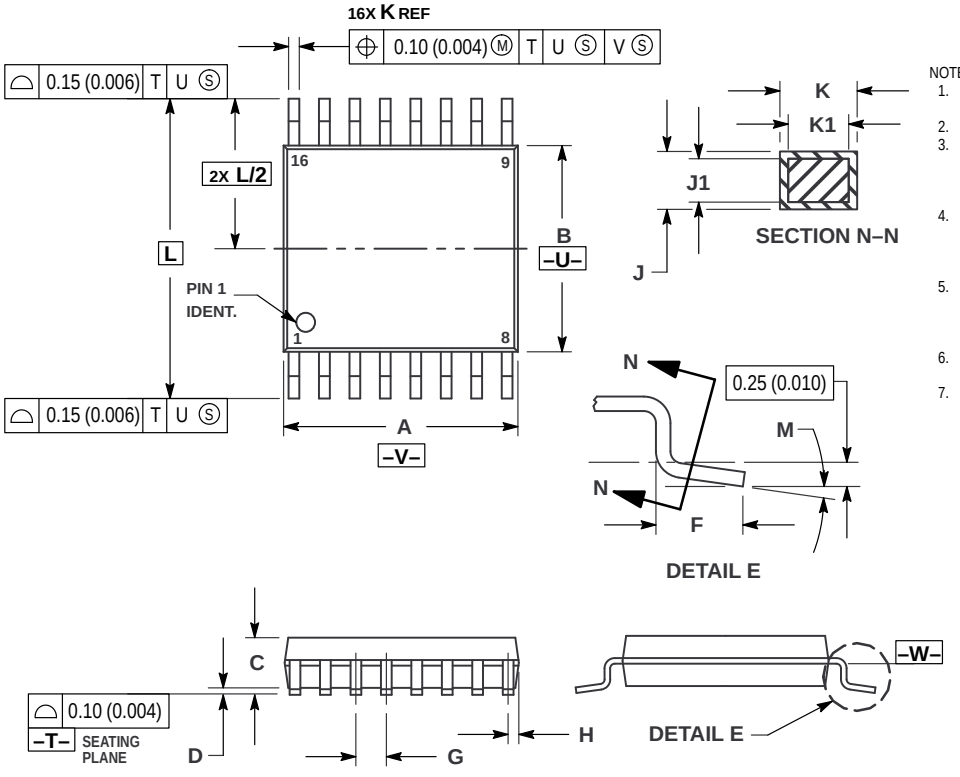
D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751B–05
ISSUE J



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

DT SUFFIX
PLASTIC TSSOP PACKAGE
CASE 948F–01
ISSUE O

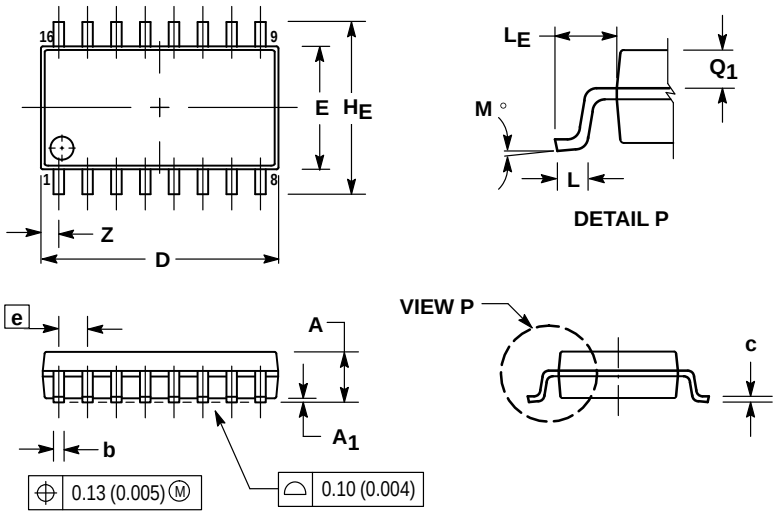


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	—	1.20	—	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

OUTLINE DIMENSIONS

M SUFFIX
PLASTIC SOIC EIAJ PACKAGE
CASE 966–01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	—	2.05	—	0.081
A_1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H_E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L_E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z	—	0.78	—	0.031

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INTERNET: http://motorola.com/sps

JAPAN: Nippon Motorola Ltd.: SPD, Strategic Planning Office, 4–32–1, Nishi–Gotanda, Shinagawa–ku, Tokyo 141, Japan. 81–3–5487–8488

ASIA / PACIFIC: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298